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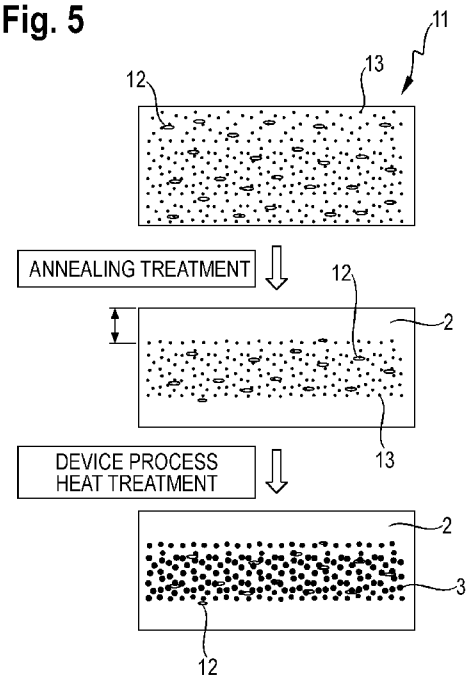
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(54) **Title**: METHOD OF MANUFACTURING ANNEALED WAFER

Fig. 5



(57) **Abstract**: Method of Manufacturing Annealed Wafer To provide a method of manufacturing an annealed wafer capable of avoiding residual voids after annealing and deterioration of TDDB characteristics of an oxide film formed on the annealed wafer, and extending the range of nitrogen concentration that can be contained in a silicon single crystal. In a method of manufacturing an annealed wafer, crystal pulling conditions are controlled such that a ratio V/G between a crystal pulling rate V and an average temperature gradient G in a crystal growth axis direction is not less than $0.9x(V/G)_{crit}$ and not more than $2.5x(V/G)_{crit}$, and a hydrogen partial pressure within a crystal pulling furnace is set to not less than 3 Pa and less than 40 Pa. A silicon single crystal has a nitrogen concentration of more than 5x1014 atoms/cm^3 and not more than $6x10^{15}$ atoms/cm^3, and a carbon concentration of not less than $1x10^{15}$ atoms/cm^3 and not more than $9x10^{15}$ atoms/cm^3, and heat treatment is performed in a noble gas atmosphere having an impurity concentration of not more than 5 ppma, or in a non-oxidizing atmosphere.

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